



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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GSID200A170S3B1

IGBT Module



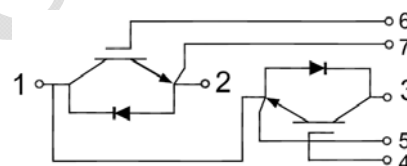
Features:

- Low Saturation Voltage: $V_{CE(sat)} = 1.60V @ I_C = 200A, T_C = 25^\circ C$
- Low Switching Loss
- 100% RBSOA Tested ($2 \times I_C$)
- Low Stray Inductance
- Lead Free, Compliant with RoHS Requirement



Applications:

- High Power Converters
- Motor Drives
- UPS Systems
- Wind Turbines



Maximum Rated Values of IGBT ($T_C = 25^\circ C$ unless otherwise specified)

V_{CES}	Collector-Emitter Blocking Voltage		1700	V
V_{GES}	Gate-Emitter Voltage		± 20	V
I_C	Continuous Collector Current	$T_C = 80^\circ C$	200	A
		$T_C = 25^\circ C$	400	A
I_{CM}	Repetitive Peak Collector Current	$T_J = 175^\circ C$	400	A
t_{SC}	Short Circuit Withstand Time		>10	μs
P_D	Maximum Power Dissipation per IGBT	$T_C = 25^\circ C$ $T_{Jmax} = 175^\circ C$	1630	W

Electrical Characteristics of IGBT ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Static characteristics

Symbol	Description	Conditions	Min	Typ	Max	Unit
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C = 1\text{mA}$, $V_{CE} = V_{GE}$	5.0	5.6	6.8	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 200\text{A}$, $V_{GE} = 15\text{V}$	$T_J = 25^{\circ}\text{C}$	1.60	1.90	V
			$T_J = 125^{\circ}\text{C}$	1.90		V
			$T_J = 150^{\circ}\text{C}$	2.00		V
I_{CES}	Collector-Emitter Leakage Current	$V_{GE} = 0\text{V}$, $V_{CE} = V_{CES}$, $T_J = 25^{\circ}\text{C}$			1	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE} = \pm 20\text{V}$, $V_{CE} = 0\text{V}$, $T_J = 25^{\circ}\text{C}$			400	nA
C_{ies}	Input Capacitance	$V_{CE} = 25\text{V}$, $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$		26		nF
C_{oes}	Output Capacitance			0.58		nF
C_{res}	Reverse Transfer Capacitance			0.42		nF

Switching Characteristics

$t_{d(on)}$	Turn-on Delay Time	$V_{CC} = 900V, I_C = 200A,$ $R_G = 10\ \Omega, V_{GE} = \pm 15V,$ Inductive Load	$T_J = 25^{\circ}C$		263		ns
			$T_J = 125^{\circ}C$		260		
			$T_J = 150^{\circ}C$		261		
t_r	Rise Time		$T_J = 25^{\circ}C$		114		ns
			$T_J = 125^{\circ}C$		120		
			$T_J = 150^{\circ}C$		119		
$t_{d(off)}$	Turn-off Delay Time		$T_J = 25^{\circ}C$		1081		ns
			$T_J = 125^{\circ}C$		1200		
			$T_J = 150^{\circ}C$		1198		
t_f	Fall Time		$T_J = 25^{\circ}C$		451		ns
			$T_J = 125^{\circ}C$		632		
			$T_J = 150^{\circ}C$		636		
E_{on}	Turn-on Switching Loss		$T_J = 25^{\circ}C$		40		mJ
			$T_J = 125^{\circ}C$		51		
			$T_J = 150^{\circ}C$		54		

E _{off}	Turn-off Switching Loss	V _{CC} = 900V, I _C =200A, R _G = 10 Ω, V _{GE} = ±15V, Inductive Load	T _J = 25℃		40		mJ
			T _J = 125℃		44		
			T _J = 150℃		48		
Q _g	Total Gate Charge		T _J = 25℃		1810		nC
			T _J = 125℃		1831		
			T _J = 150℃		1839		
RBSOA	Reverse Bias Safe Operation Area	I _C =400A, V _{CC} =1630V, V _p =1700V, R _g = 10Ω, V _{GE} =+15V to 0V, T _J =150℃	Trapezoid				
SCSOA	Short Circuit Safe Operation Area	V _{CC} ≤ 900V, V _{GE} = 15V, T _J = 150℃	10			μs	
R _{θJC}	IGBT Thermal Resistance: Junction-To-Case				0.092		℃/W

Maximum Rated Values of Diode ($T_C = 25^\circ C$ unless otherwise specified)

V_{RRM}	Repetitive Peak Reverse Voltage	1700	V
I_F	Diode Continuous Forward Current	100	A
I_{FM}	Diode Maximum Forward Current	200	A

Electrical Characteristics of Diode ($T_C = 25^\circ C$ unless otherwise specified)

Symbol	Description	Conditions		Min	Typ	Max	Unit	
V _{FM}	Forward Voltage	I _F = 200A , V _{GE} = 0V	T _J = 25°C		2.10		V	
			T _J = 125°C		2.20			
I _{rr}	Peak Reverse Recovery Current	I _F = 200A, di/dt = 896A/μs, V _{rr} = 900V, V _{GE} = -15V	T _J = 25°C		110		A	
			T _J = 125°C		144			
Q _{rr}	Reverse Recovery Charge		T _J = 25°C		20.5		μC	
			T _J = 125°C		38.1			
E _{rec}	Reverse Recovery Energy		T _J = 25°C		9.8		mJ	
			T _J = 125°C		20.6			
R _{θJC}	Diode Thermal Resistance: Junction-To-Case				0.111		°C/W	

Module

Symbol	Description		Min	Typ	Max	Unit
V _{iso}	Isolation Voltage(All Terminals Shorted)	f = 50Hz, 1minute			2500	V
T _J	Maximum Junction Temperature				175	°C
T _{JOP}	Maximum Operating Junction Temperature Range		-40		+150	°C
T _{stg}	Storage Temperature		-40		+125	°C
R _{θCS}	Case-To-Sink (Conductive Grease Applied)			0.03		°C/W
T	Power Terminals Screw:M6		3.0		5.0	N·m
T	Mounting Screw:M6		4.0		6.0	N·m
G	Weight			300		g

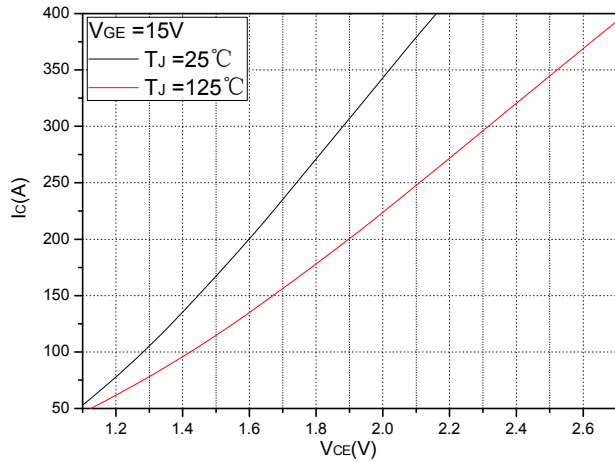


Fig.1 Typical Saturation Voltage Characteristics

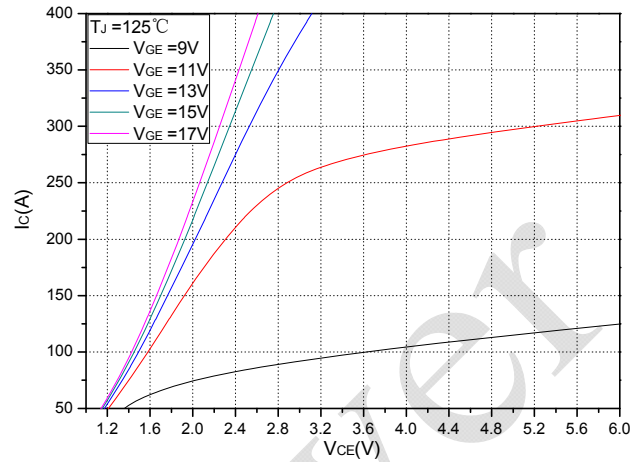


Fig.2 Typical Output Characteristics

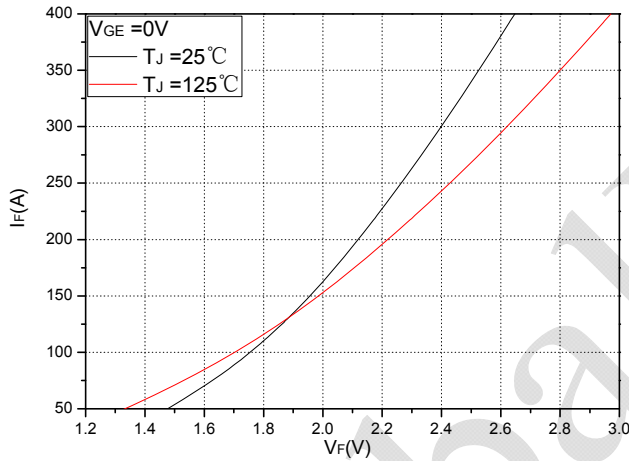


Fig.3 Forward Characteristics of FWD

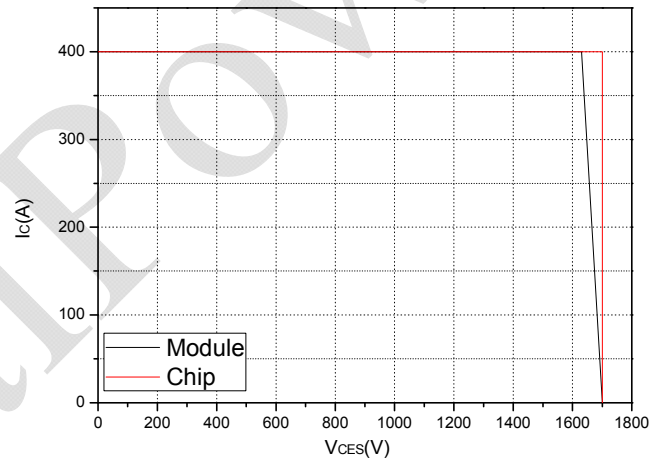


Fig.4 Reverse Bias Safe Operation Area (RBSOA)

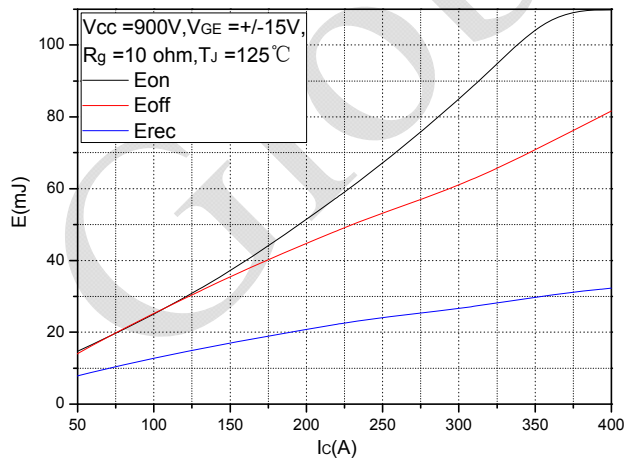


Fig.5 Typical Switching Loss vs. Collector Current

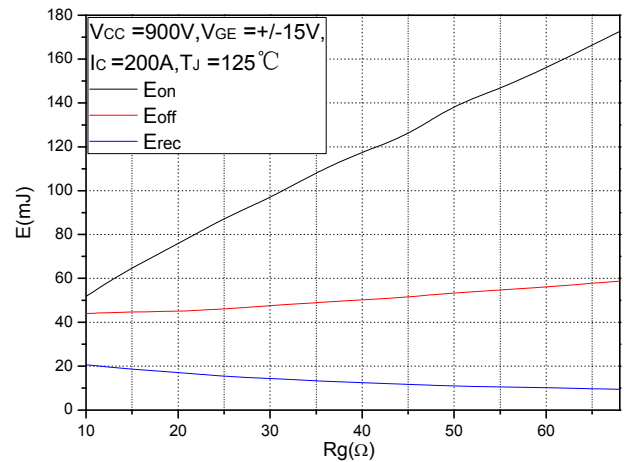


Fig.6 Typical Switching Losses vs. Gate Resistance

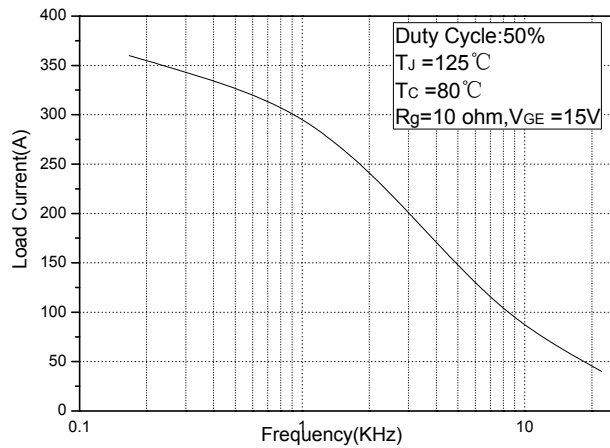


Fig.7 Typical Load Current vs. Frequency

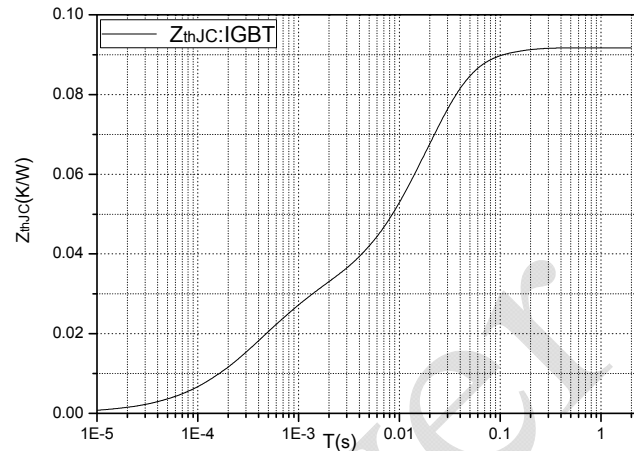


Fig.8 Transient thermal impedance (IGBT)

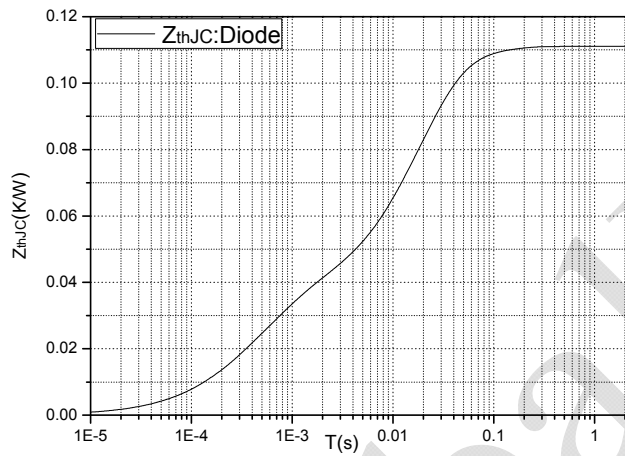
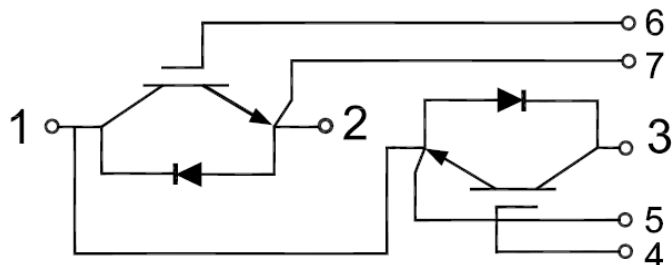
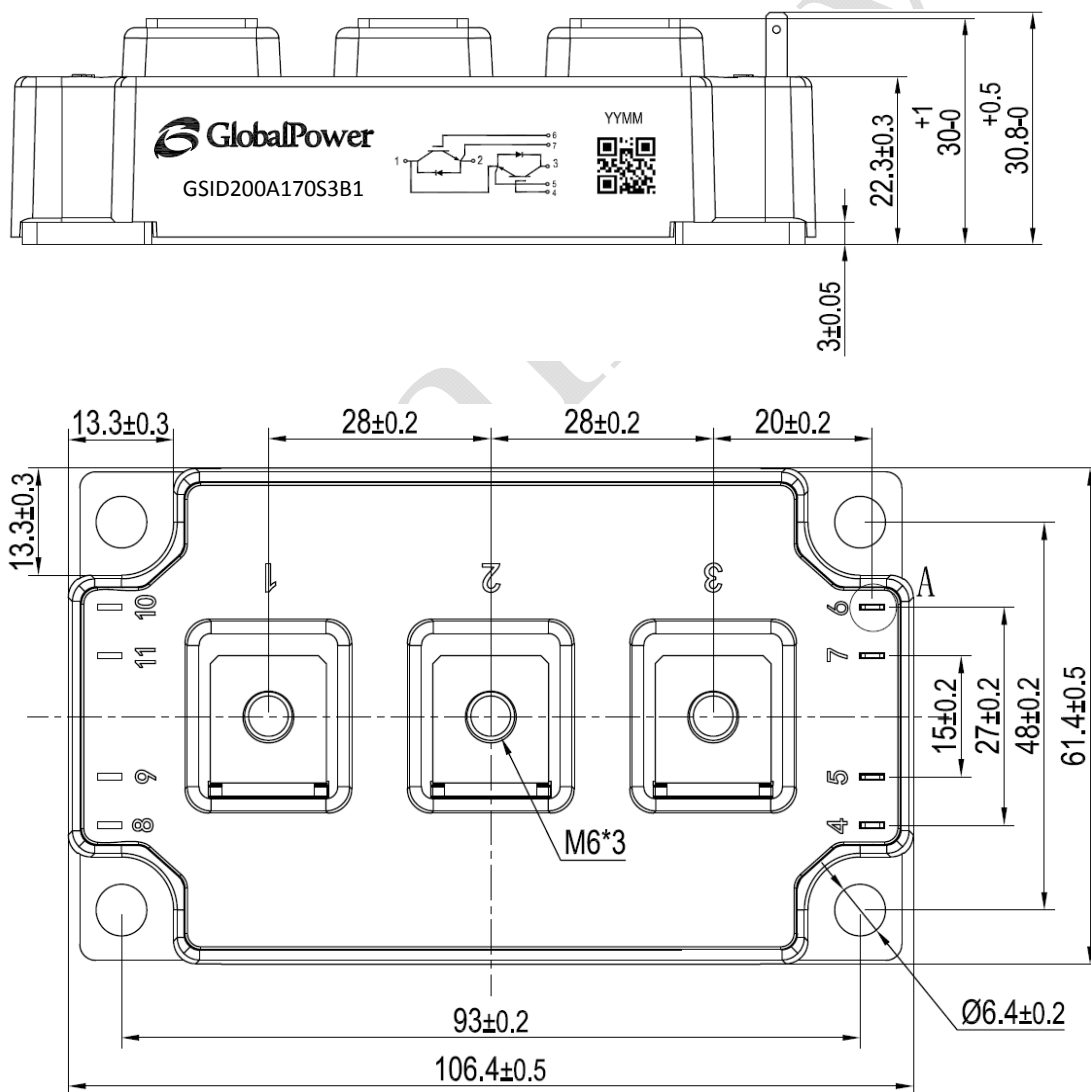


Fig.9 Transient thermal impedance (Diode)

Internal Circuit



Package Outline (Unit: mm):



Revision History

Date	Revision	Notes
10/23/2015	0.1	Initial release

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Notes

- RoHS Compliance**
 The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented March, 2013. RoHS Declarations for this product can be obtained from the Product Documentation sections of www.gptechgroup.com.
- REACH Compliance**
 REACH substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact our office at GPTG Headquarters in Lake Forest, California to insure you get the most up-to-date REACH SVHC Declaration.
 REACH banned substance information (REACH Article 67) is also available upon request.
- This product has not been designed or tested for use in, and is not intended for use in, applications implanted into the human body nor in applications in which failure of the product could lead to death, personal injury or property damage, including but not limited to equipment used in the operation of nuclear facilities, life-support machines, cardiac defibrillators or similar emergency medical equipment, aircraft navigation or communication or control systems, or air traffic control.
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